

DCR803SG

Phase Control Thyristor

Supersedes January 2000 version, DS4451-4.0

DS4451-5.0 July 2001

FEATURES

- Double Side Cooling
- High Surge Capability
- High Mean Current
- Fatigue Free

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- DC Motor Control

VOLTAGE RATINGS

Type Number	Repetitive Peak Voltages V _{DRM} V _{RRM} V	Conditions
DCR803SG18	1800	$T_{ij} = 0^{\circ} \text{ to } 125^{\circ}\text{C},$
DCR803SG17	1700	$I_{DRM}^{v_j} = I_{RRM} = 50 \text{mA},$
DCR803SG16	1600	V_{DRM} , V_{RRM} $t_p = 10ms$,
DCR803SG15	1500	V _{DSM} & V _{RSM} =
DCR803SG14	1400	V _{DRM} & V _{RRM} + 100V
		respectively

Lower voltage grades available.

Outline type code: G. See Package Details for further information.

KEY PARAMETERS

1800V

1045A

14000A

1000A/μ**s**

dVdt $1000V/\mu s$

 $\mathbf{V}_{\mathtt{DRM}}$

I_{T(AV)}

ITSM

dl/dt

Fig. 1 Package outline

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR806SG26

Note: Please use the complete part number when ordering and quote this number in any future correspondance relating to your order.



CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Conditions	Max.	Units		
Double Sic	le Cooled					
I _{T(AV)}	Mean on-state current	Half wave resistive load	1045	А		
I _{T(RMS)}	RMS value	-	1641	А		
I _T	Continuous (direct) on-state current	-	1450	А		
Single Side Cooled (Anode side)						
I _{T(AV)}	Mean on-state current	Half wave resistive load	675	Α		
I _{T(RMS)}	RMS value	-	1060	А		
I _T	Continuous (direct) on-state current	-	862	А		

CURRENT RATINGS

 T_{case} = 80°C unless stated otherwise

Symbol	Parameter	Conditions	Max.	Units			
Double Sic	Double Side Cooled						
I _{T(AV)}	Mean on-state current	Half wave resistive load	820	А			
I _{T(RMS)}	RMS value	-	1285	А			
I _T	Continuous (direct) on-state current	-	1085	А			
Single Side	Single Side Cooled (Anode side)						
I _{T(AV)}	Mean on-state current	Half wave resistive load	505	А			
I _{T(RMS)}	RMS value	-	793	А			
I _T	Continuous (direct) on-state current	-	620	А			



SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	11.2	kA
l²t	I ² t for fusing	$V_R = 50\% V_{RRM} - 1/4 \text{ sine}$	625 x 10 ³	A²s
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	14.0	kA
l²t	I ² t for fusing	$V_R = 0$	975 x 10 ³	A²s

THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled	dc	-	0.032	°C/W
		Single side cooled	Anode dc	-	0.064	°C/W
			Cathode dc	-	0.064	°C/W
	Thermal resistance - case to heatsink	Clamping force 12.5kN with mounting compound	Double side	-	0.008	°C/W
R _{th(c-h)}			Single side	-	0.016	°C/W
_	Virtual junction temperature	On-state (conducting)		-	135	°C
$T_{v_{j}}$		Reverse (blocking)		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
-	Clamping force			11.0	13.0	kN



DYNAMIC CHARACTERISTICS

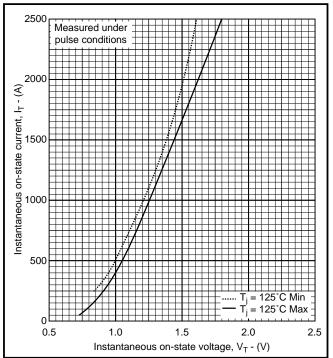
Symbol	Parameter	Conditions		Тур.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	50	mA
dV/dt	Maximum linear rate of rise of off-state voltage	To 67% V_{DRM} T_j = 125°C. Gate open circuit.		-	1000	V/µs
		Gate source 1.5A	Repetitive 50Hz	-	500	A/μs
dl/dt	Rate of rise of on-state current		Non-repetitive	-	1000	A/μs
V _{T(TO)}	Threshold voltage	At T _{vj} = 125°C		-	0.85	V
r _T	On-state slope resistance	At T _{vj} = 125°C		-	0.38	mΩ
t _{gd}	Delay time	$V_D = 67\% V_{DRM}$, Gate source 30V, 15 Ω t, = 0.5 μ s, $T_j = 25$ °C		-	1.5	μs
t _q	Turn-off time	$I_T = 1000A$, $t_p = 1ms$, $T_j = 125$ °C, $V_R = 50V$, $dI_{RR}/dt = 20A/\mu s$, $V_{DR} = 67\% V_{DRM}$, $dV_{DR}/dt = 20V/\mu s$ linear		200	300	μs
I _L	Latching current	$T_{j} = 25^{\circ}C, V_{D} = 5V$		350	1000	mA
I _H	Holding current	$T_{j} = 25^{\circ}C, V_{D} = 5V$		40	100	mA

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Conditions	Тур.	Max.	Units
$V_{\rm GT}$	Gate trigger voltage	V _{DRM} = 5V, T _{case} = 25°C	1.0	3.5	V
I _{GT}	Gate trigger current	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	-	200	mA
V _{GD}	Gate non-trigger voltage	At V _{DRM} T _{case} = 125°C	-	0.25	V
I _{GD}	Gate non-trigger current	At V _{DRM} T _{case} = 125°C	-	-	А
V _{FGM}	Peak forward gate voltage	Anode positive with respect to cathode	-	30	V
V _{FGN}	Peak forward gate voltage	Anode negative with respect to cathode	-	0.25	V
V_{RGM}	Peak reverse gate voltage		-	5	V
I _{FGM}	Peak forward gate current	Anode positive with respect to cathode	-	30	А
P _{GM}	Peak gate power	See table, gate characteristics curve	-	150	W
$P_{G(AV)}$	Mean gate power		-	10	W



CURVES



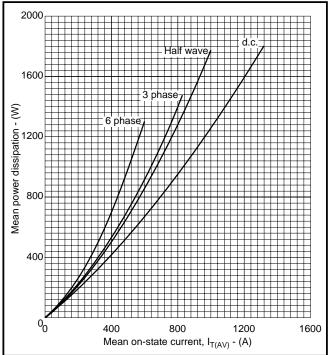


Fig.2 Maximum (limit) on-state characteristics

Fig.3 Dissipation curves

 V_{TM} Equation:-

$$V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$$

Where A = 0.464203

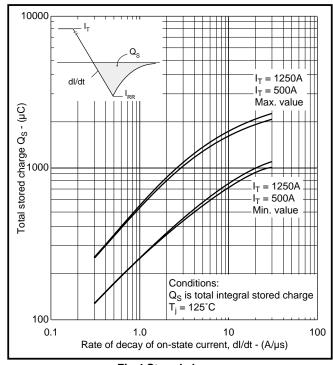
B = 0.51516

C = 0.000249

D = 0.005951

these values are valid for $T_j = 125^{\circ}C$ for $I_T 500A$ to 2500A





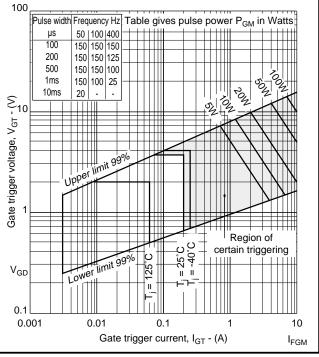


Fig.4 Stored charge

Fig.5 Gate characteristics

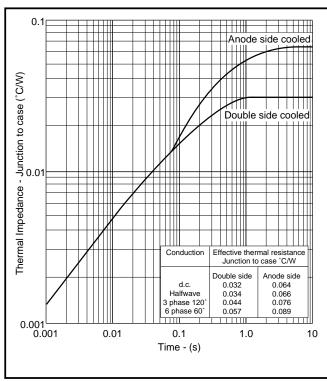


Fig.6 Maximum (limit) transient thermal impedance - junction to case

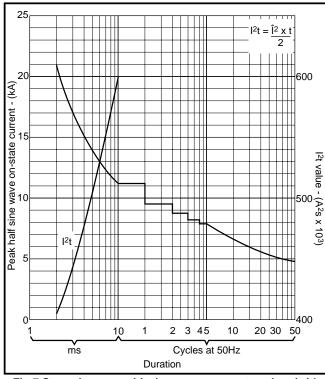
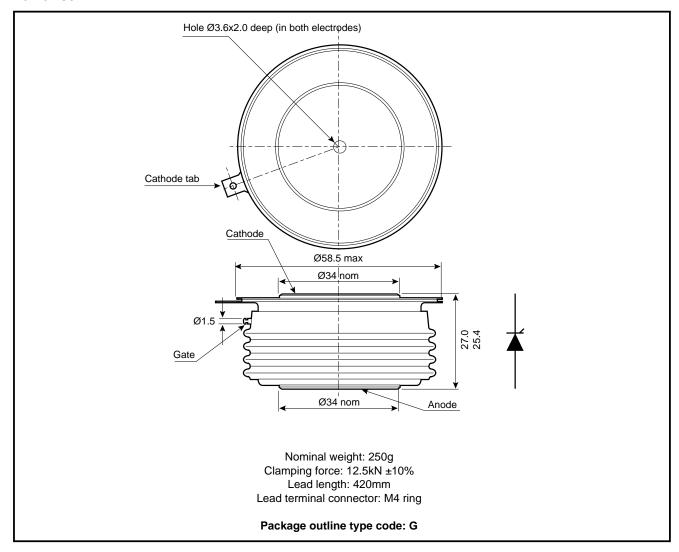


Fig.7 Surge (non-repetitive) on-state current vs time (with 50% $\rm V_{RRM}$ at $\rm T_{case}\,125^{\circ}C)$



PACKAGE DETAILS

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink / clamping systems in line with advances in device types and the voltage and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group continues to offer high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the up to date CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete solution (PACs).

DEVICE CLAMPS

Disc devices require the correct clamping force to ensure their safe operation. The PACs range offers a varied selection of pre-loaded clamps to suit all of our manufactured devices. This include cube clamps for single side cooling of 'T' 22mm

Clamps are available for single or double side cooling, with high insulation versions for high voltage assemblies.

Please refer to our application note on device clamping, AN4839

HEATSINKS

Power Assembly has its own proprietary range of extruded aluminium heatsinks. They have been designed to optimise the performance or our semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest Sales Representative or Customer Services.



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Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

Advance Information: The product design is complete and final characterisation for volume production is well in hand.

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